MMT05B230T3, MMT05B260T3, MMT05B310T3

Preferred Devices

Thyristor Surge Protectors
High Voltage Bidirectional TSPD

These Thyristor Surge Protective devices (TSPD) prevent overvoltage damage to sensitive circuits by lightning, induction and power line crossings. They are breakover−triggered crowbar protectors. Turn−off occurs when the surge current falls below the holding current value.

Secondary protection applications for electronic telecom equipment at customer premises.

Features

- High Surge Current Capability: 50 A 10 x 1000 µsec, for Controlled Temperature Environments
- The MMT05B230T3 Series is used to help equipment meet various regulatory requirements including: Bellcore 1089, ITU K.20 & K.21, IEC 950, UL 1459 & 1950 and FCC Part 68
- Bidirectional Protection in a Single Device
- Little Change of Voltage Limit with Transient Amplitude or Rate
- Freedom from Wearout Mechanisms Present in Non−Semiconductor Devices
- Fail−Safe, Shorts When Overstressed, Preventing Continued Unprotected Operation
- Surface Mount Technology (SMT)
- ℔ Indicates UL Registered – File #E210057
- Pb−Free Packages are Available

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Off−State Voltage – Maximum MMT05B230T3 MMT05B260T3 MMT05B310T3	V_{DM}	 ± 170 ± 200 ± 270	V
Maximum Pulse Surge Short Circuit Current Non−Repetitive Double Exponential Decay Waveform (Notes 1 and 2) (−25°C Initial Temperature) 8 x 20 µsec 10 x 160 µsec 10 x 560 µsec 10 x 1000 µsec	 I_{PPS1} I_{PPS2} I_{PPS3} I_{PPS4}	 ± 150 ± 100 ± 70 ± 50	A(pk)
Maximum Non−Repetitive Rate of Change of On−State Current Double Exponential Waveform, R = 1.0, L = 1.5 µH, C = 1.67 µF, I_{pk} = 110A	di/dt	± 150	A/µs

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.
1. Allow cooling before testing second polarity.
2. Measured under pulse conditions to reduce heating.
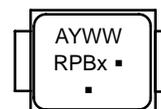
ON Semiconductor®

http://onsemi.com

BIDIRECTIONAL TSPD (℔)
50 AMPERE SURGE
265 thru 365 VOLTS

MT1 ○—————————○ MT2

SMB
(No Polarity)
(Essentially JEDEC DO−214AA)
CASE 403C

MARKING DIAGRAMS

AYWW
RPBx ▪
▪

RPBx = Device Code
    x = G or J
Y   = Year
WW = Work Week
▪   = Pb−Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Operating Temperature Range Blocking or Conducting State	T_{J1}	−40 to +125	°C
Overload Junction Temperature – Maximum Conducting State Only	T_{J2}	+175	°C
Instantaneous Peak Power Dissipation (I_{pk} = 50 A, 10x1000 µsec @ 25°C)	P_{PK}	2000	W
Maximum Lead Temperature for Soldering Purposes 1/8″ from Case for 10 Seconds	T_L	260	°C

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted) Devices are bidirectional. All electrical parameters apply to forward and reverse polarities.

Characteristics	Symbol	Min	Typ	Max	Unit

Breakover Voltage (Both polarities) (dv/dt = 100 V/µs, I_{SC} = 1.0 A, Vdc = 1000 V)   MMT05B230T3
    MMT05B260T3
    MMT05B310T3
(+65°C)
    MMT05B230T3
    MMT05B260T3
    MMT05B310T3
	$V_{(BO)}$	–
		–
		–
		
		–
		–
		–
			–
			–
			–
			
			–
			–
			–
				265
				320
				365
				
				280
				340
				400
					V

Breakover Voltage (Both polarities) (f = 60 Hz, I_{SC} = 1.0 A(rms), V_{OC} = 1000 V(rms), R_I = 1.0 kΩ, t = 0.5 cycle) (Note 3)   MMT05B230T3
    MMT05B260T3
    MMT05B310T3
(+65°C)
    MMT05B230T3
    MMT05B260T3
    MMT05B310T3
	$V_{(BO)}$	–
		–
		–
		
		–
		–
		–
			–
			–
			–
			
			–
			–
			–
				265
				320
				365
				
				280
				340
				400
					V

Breakover Voltage Temperature Coefficient	$dV_{(BO)}/dT_J$	–	0.08	–	%/°C

Breakdown Voltage ($I_{(BR)}$ = 1.0 mA) Both polarities   MMT05B230T3
    MMT05B260T3
    MMT05B310T3
	$V_{(BR)}$	–
		–
		–
			190
			240
			280
				–
				–
				–
					V

Off State Current (V_{D1} = 50 V) Both polarities (V_{D2} = V_{DM}) Both polarities	I_{D1} I_{D2}	– –	– –	2.0 5.0	µA
On–State Voltage (I_T = 1.0 A) (PW ≤ 300 µs, Duty Cycle ≤ 2%) (Note 3)	V_T	–	1.53	3.0	V
Breakover Current (f = 60 Hz, V_{DM} = 1000 V(rms), R_S = 1.0 kΩ) – Both polarities	I_{BO}	–	230	–	mA
Holding Current (Both polarities) (Note 3) V_S = 500 V; I_T (Initiating Current) = ± 1.0 A	I_H	150	340	–	mA
Critical Rate of Rise of Off–State Voltage (Linear waveform, V_D = Rated V_{BR}, T_J = 25°C)	dv/dt	2000	–	–	V/µs
Capacitance (f = 1.0 MHz, 50 Vdc, 1.0 V rms Signal) (f = 1.0 MHz, 2.0 Vdc, 15 mV rms Signal)	C_O	– –	22 53	– 75	pF

3. Measured under pulse conditions to reduce heating.

MMT05B230T3, MMT05B260T3, MMT05B310T3

Voltage Current Characteristic of TSPD
(Bidirectional Device)

Symbol	Parameter
I_{D1}, I_{D2}	Off State Leakage Current
V_{D1}, V_{D2}	Off State Blocking Voltage
V_{BR}	Breakdown Voltage
V_{BO}	Breakover Voltage
I_{BO}	Breakover Current
I_{H}	Holding Current
V_{TM}	On State Voltage
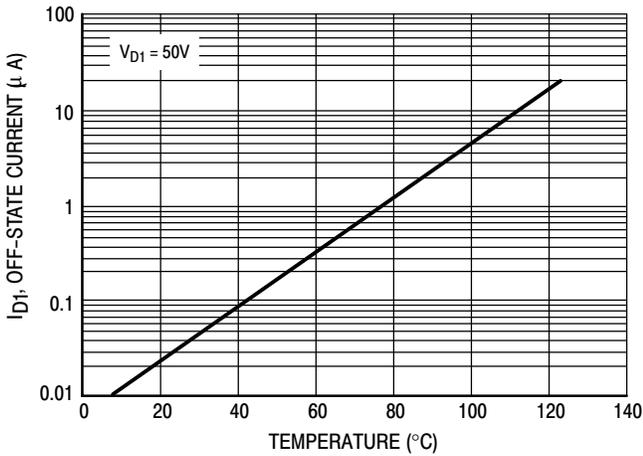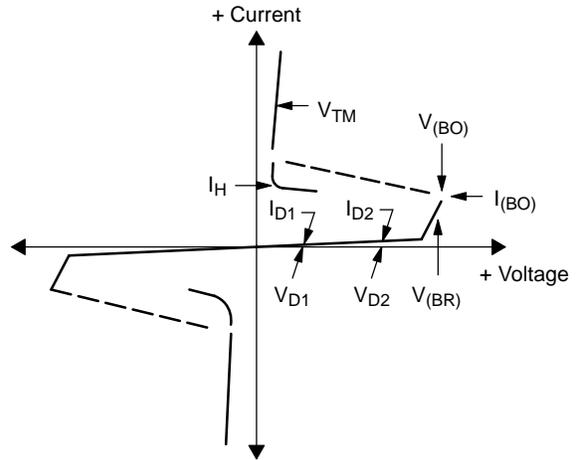
Figure 1. Off–State Current versus Temperature
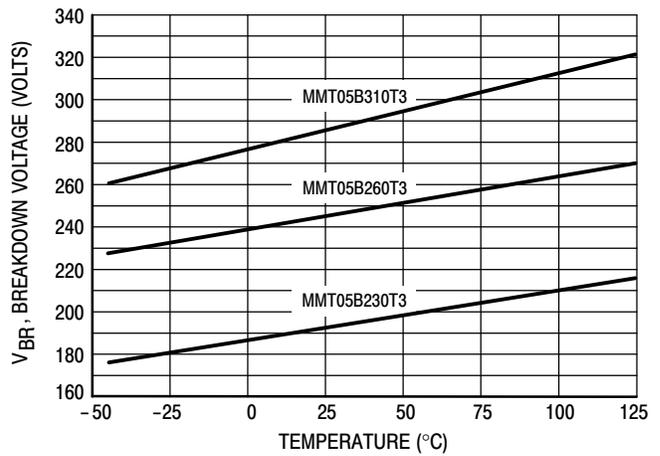
Figure 2. Breakdown Voltage versus Temperature
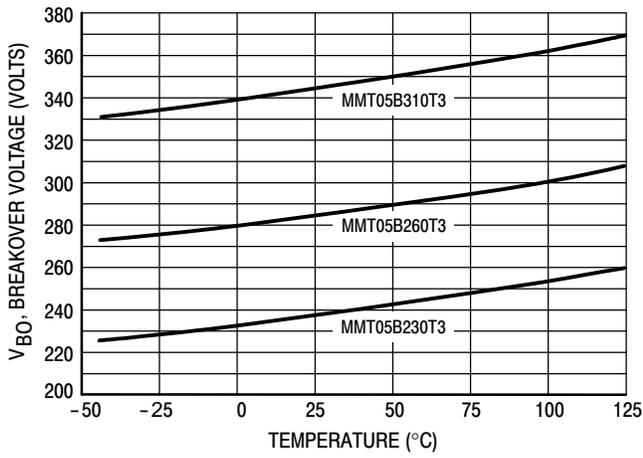
Figure 3. Breakover Voltage versus Temperature
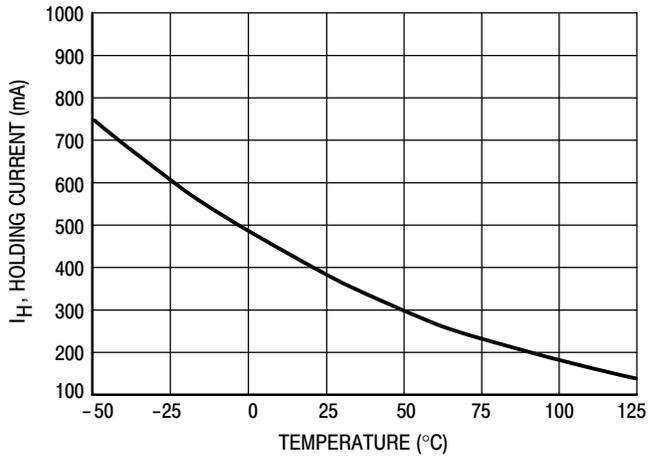
Figure 4. Holding Current versus Temperature
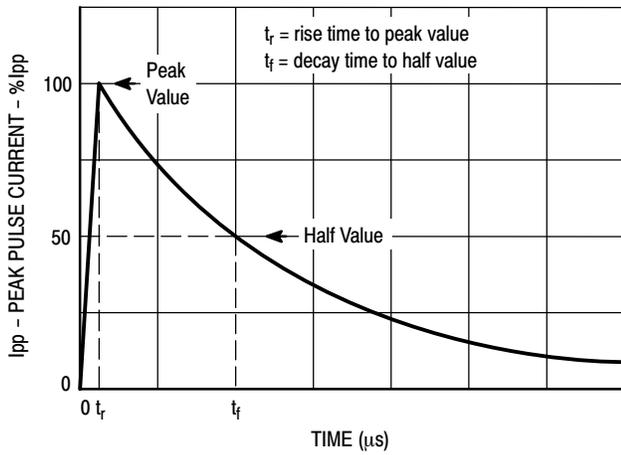
Figure 5. Exponential Decay Pulse Waveform
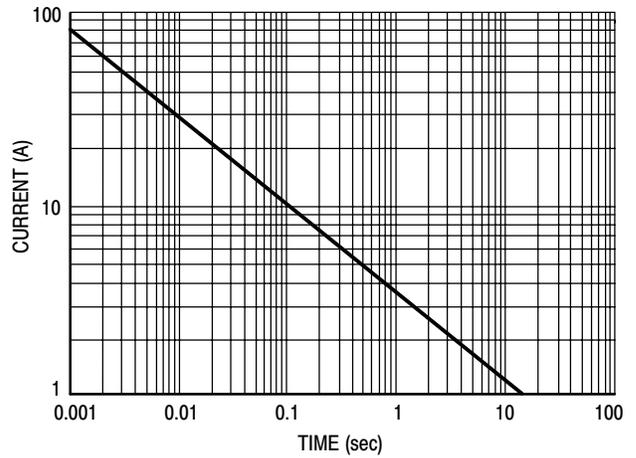
Figure 6. Peak Surge On–State Current versus
Surge Current Duration, Sinusoidal Waveform

MMT05B230T3, MMT05B260T3, MMT05B310T3

*Polymeric PTC (positive temperature coefficient) overcurrent protection device
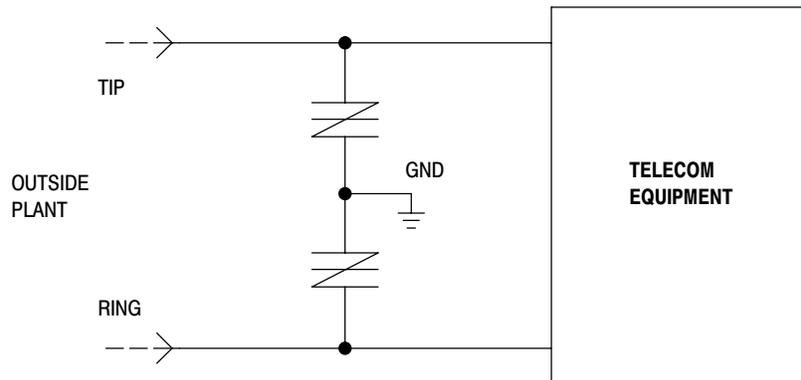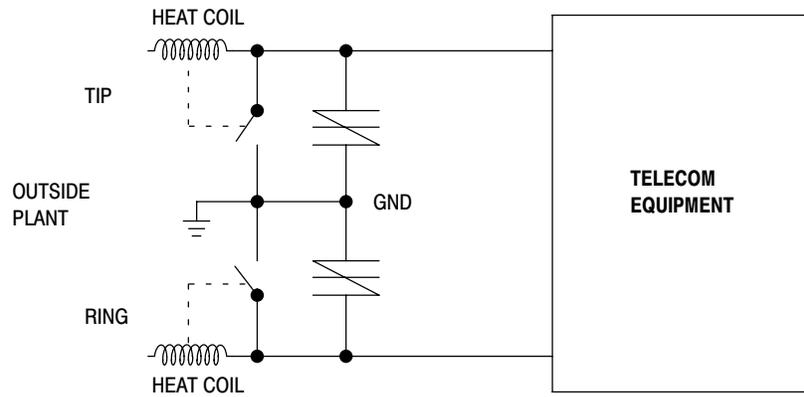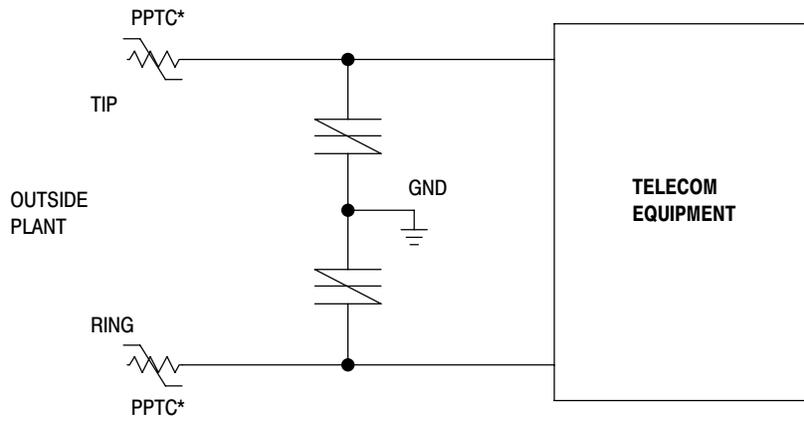
ORDERING INFORMATION

Device	Package	Shipping†
MMT05B230T3	SMB	
MMT05B230T3G	SMB (Pb−Free)	
MMT05B260T3	SMB	
MMT05B260T3G	SMB (Pb−Free)	2500 / Tape & Reel
MMT05B310T3	SMB	
MMT05B310T3G	SMB (Pb−Free)	

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMT05B230T3, MMT05B260T3, MMT05B310T3

PACKAGE DIMENSIONS

SMB
(No Polarity)
(Essentially JEDEC DO−214AA)
CASE 403C−01
ISSUE A
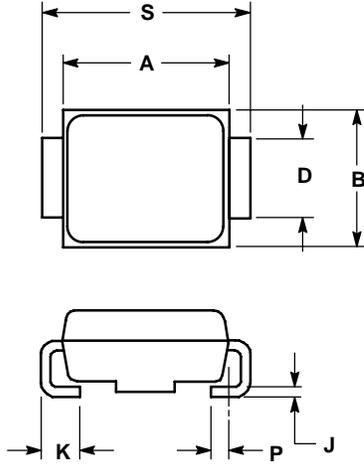
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. D DIMENSION SHALL BE MEASURED WITHIN DIMENSION P.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.160	0.180	4.06	4.57
B	0.130	0.150	3.30	3.81
C	0.075	0.095	1.90	2.41
D	0.077	0.083	1.96	2.11
H	0.0020	0.0060	0.051	0.152
J	0.006	0.012	0.15	0.30
K	0.030	0.050	0.76	1.27
P	0.020 REF		0.51 REF	
S	0.205	0.220	5.21	5.59

SOLDERING FOOTPRINT*

$\dfrac{0.089}{2.261}$

$\dfrac{0.108}{2.743}$

$\dfrac{0.085}{2.159}$

$\left(\dfrac{\text{inches}}{\text{mm}}\right)$
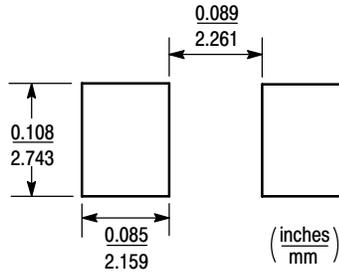
*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MMT05B230T3/D